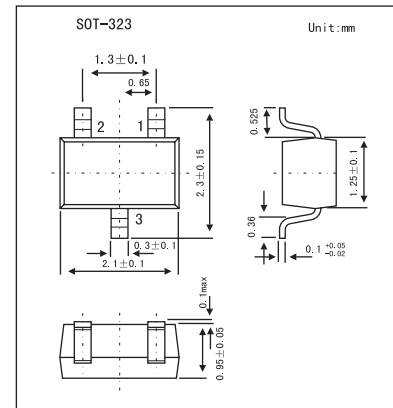
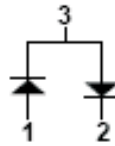


High Voltage Switching Diode KMSD2004S(CMSD2004S)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Continuous reverse voltage	V _R	240	V
Peak repetitive reverse voltage	V _{RRM}	300	V
Peak repetitive reverse current	I _o	200	mA
Continuous forward current	I _F	225	mA
Peak repetitive forward current	I _{FRM}	625	mA
Forward surge current tp=1 μs	I _{FSM}	4000	mA
tp=1s		1000	mA
Power dissipation	P _D	250	mW
Thermal Resistance.Junction-to-Ambient	R _{thJA}	500	°C/W
Operating and storage Junction temperature	T _J ,T _{stg}	-65 to 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{(BR)R}	I _R =100 μA	300			V
Forward Voltage	V _F	I _F = 100mA			-	V
Peak Reverse Current	I _R	V _R = 200V			-	nA
		V _R = 200V, T _A = 150°C			-	μA
		V _R = 240V			100	nA
		V _R = 240V, T _A = 150°C			100	μA
Junction Capacitance	C _j	V _R = 0, f = 1.0MHz			5	pF
Reverse Recovery Time	t _{rr}	I _F = I _R =30mA,Recov.to 3.0mA, R _L = 100 Ω			50	ns

■ Marking

Marking	B6D